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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Wing-Cheong G. Lai et al.

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Examiner: Tuan Ouach

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PATENT

ŠMALL GRAIN SIZE, CONFORMAL ALUMINUM INTERCONNECTS AI

METHOD FOR THEIR FORMATION

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

nmissioner for Patents Washington, D.C. 20231

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Applicant has reviewed the Office Action mailed on November 20, 2002. Please amend the above-identified patent application as follows.

IN THE CLAIMS

Please substitute the claim set in the appendix entitled Clean Version of Pending Gaims for the previously pending claim set. The substitute claim set is intended to reflect amondment of previously pending claims 17, 29, 37-39, and 45. The specific amendments to individual claims are detailed in the following marked up set of claims.

17. An interconnect structure in an integrated circuit, comprising: (Amended) a first layer of titanium nitride; an aluminum film;

a second layer of titanium nitride between the first layer of titanium nitride and the aluminum film wherein the second layer of titanium nitride comprises a polycrystalline orientation that comprises a mixture of 1:1 of <111> and <200> oriented grains that are effective for forming an aluminum film of small grain size.

29. (Amended) An interconnect structure in an interconnect via defined by a bottom surface, a top surface, and sidewalls, comprising:

a first layer of titanium nitride formed on the sidewalls and the bottom surface defining the interconnect via;

a second layer of titanium nitride supported by the first layer of titanium nitride; and





